

## MM54HC173/MM74HC173 TRI-STATE® Quad D Flip-Flop

### General Description

The MM54HC173/MM74HC173 is a high speed TRI-STATE QUAD D TYPE FLIP-FLOP that utilizes advanced silicon-gate CMOS technology. It possesses the low power consumption and high noise immunity of standard CMOS integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky device. The outputs are buffered, allowing this circuit to drive 15 LS-TTL loads. The large output drive capability and TRI-STATE feature make this part ideally suited for interfacing with bus lines in a bus oriented system.

The four D TYPE FLIP-FLOPS operate synchronously from a common clock. The TRI-STATE outputs allow the device to be used in bus organized systems. The outputs are placed in the TRI-STATE mode when either of the two output disable pins are in the logic "1" level. The input disable allows the flip-flops to remain in their present states without having to disrupt the clock. If either of the 2 input disables are taken to a logic "1" level, the Q outputs are fed back to

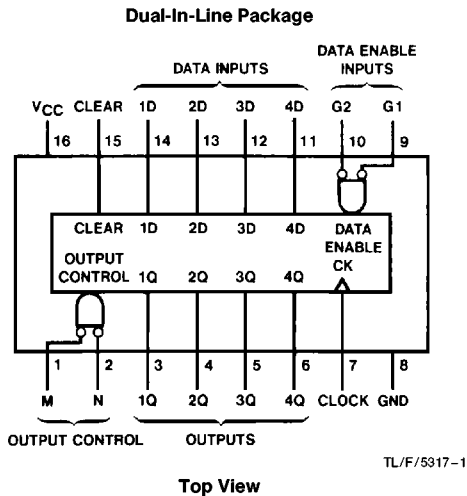
the inputs, forcing the flip flops to remain in the same state. Clearing is enabled by taking the CLEAR input to a logic "1" level. The data outputs change state on the positive going edge of the clock.

The 54HC/74HC logic family is functionally as well as pin-out compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

### Features

- Typical propagation delay: 18 ns
- Wide operating supply voltage range: 2–6V
- TRI-STATE outputs
- Low input current: 1  $\mu$ A maximum
- Low quiescent supply current: 80  $\mu$ A maximum (74HC)
- High output drive current: 6 mA minimum

### Connection Diagram



Order Number MM54HC173 or MM74HC173

### Truth Table

Clear	Clock	Inputs		Data D	Output Q
		G1	G2		
H	X	X	X	X	L
L	L	X	X	X	$Q_0$
L	↑	H	X	X	$Q_0$
L	↑	X	H	X	$Q_0$
L	↑	L	L	L	L
L	↑	L	L	H	H

When either M or N (or both) is (are) high the output is disabled to the high-impedance state; however, sequential operation of the flip-flops is not affected.

H = high level (steady state)  
 L = low level (steady state)  
 ↑ = low-to-high level transition  
 X = don't care (any input including transitions)  
 $Q_0$  = the level of Q before the indicated steady state input conditions were established

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## Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ( $V_{CC}$ )	-0.5 to +7.0V
DC Input Voltage ( $V_{IN}$ )	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage ( $V_{OUT}$ )	-0.5 to $V_{CC} + 0.5V$
Clamp Diode Current ( $I_{IK}, I_{OK}$ )	$\pm 20$ mA
DC Output Current, per pin ( $I_{OUT}$ )	$\pm 35$ mA
DC $V_{CC}$ or GND Current, per pin ( $I_{CC}$ )	$\pm 70$ mA
Storage Temperature Range ( $T_{STG}$ )	-65°C to +150°C
Power Dissipation ( $P_D$ )	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature ( $T_L$ )	
(Soldering 10 seconds)	260°C

## Operating Conditions

	Min	Max	Units
Supply Voltage ( $V_{CC}$ )	2	6	V
DC Input or Output Voltage ( $V_{IN}, V_{OUT}$ )	0	$V_{CC}$	V
Operating Temp. Range ( $T_A$ )			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times ( $t_r, t_f$ )			
$V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

## DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$			Units	
				74HC $T_A = -40$ to $85^\circ C$		54HC $T_A = -55$ to $125^\circ C$		
				Typ	Guaranteed Limits			
$V_{IH}$	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
$V_{IL}$	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	0.5	V
			4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
$V_{OH}$	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 6.0$ mA $ I_{OUT}  \leq 7.8$ mA	4.5V		3.98	3.84	3.7	V
			6.0V		5.48	5.34	5.2	V
$V_{OL}$	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 6.0$ mA $ I_{OUT}  \leq 7.8$ mA	4.5V		0.26	0.33	0.4	V
			6.0V		0.26	0.33	0.4	V
$I_{IN}$	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		$\pm 0.1$	$\pm 1.0$	$\pm 1.0$	$\mu A$
$I_{OZ}$	Maximum TRI-STATE Output Leakage	$V_{OUT} = V_{CC}$ or GND Enable = $V_{IH}$	6.0V		$\pm 0.5$	$\pm 5.0$	$\pm 10$	$\mu A$
$I_{CC}$	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		8.0	80	160	$\mu A$

**Note 1:** Absolute Maximum Ratings are those values beyond which damage to the device may occur.

**Note 2:** Unless otherwise specified all voltages are referenced to ground.

**Note 3:** Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

**Note 4:** For a power supply of 5V  $\pm 10\%$  the worst case output voltages ( $V_{OH}$ , and  $V_{OL}$ ) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case  $V_{IH}$  and  $V_{IL}$  occur at  $V_{CC} = 5.5V$  and 4.5V respectively. (The  $V_{IH}$  value at 5.5V is 3.85V.) The worst case leakage current ( $I_{IN}$ ,  $I_{CC}$ , and  $I_{OZ}$ ) occur for CMOS at the higher voltage and so the 6.0V values should be used.

\*\* $V_{IL}$  limits are currently tested at 20% of  $V_{CC}$ . The above  $V_{IL}$  specification (30% of  $V_{CC}$ ) will be implemented no later than Q1, CY'89.

<b>AC Electrical Characteristics</b> $V_{CC}=5V, T_A=25^{\circ}C, C_L=45\text{ pF}, t_r=t_f=6\text{ ns}$					
Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
$f_{MAX}$	Maximum Operating Frequency		45	30	MHz
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay: Clock to Q			31	ns
$t_{PHL}$	Maximum Propagation Delay: Clear to Q		18	27	ns
$t_{PZH}, t_{PZL}$	Maximum Output Enable Time	$R_L = 1\text{ k}\Omega$	18	28	ns
$t_{PHZ}, t_{PLZ}$	Maximum Output Disable Time	$R_L = 1\text{ k}\Omega$ $C_L = 5\text{ pF}$	16	25	ns
$t_S$	Minimum Data Setup Time			20	ns
$t_{SE}$	Minimum Data Enable Setup Time			20	ns
$t_H$	Minimum Data Hold Time			0	ns
$t_{HE}$	Minimum Data Enable Hold Time			0	ns
$t_W$	Minimum Clock Pulse Width			16	ns

<b>AC Electrical Characteristics</b> $V_{CC}=2.0V\text{ to }6.0V, C_L=50\text{ pF}, t_r=t_f=6\text{ ns}$ (unless otherwise specified)								
Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^{\circ}C$		74HC	54HC	Units
						$T_A = -40\text{ to }85^{\circ}C$	$T_A = -55\text{ to }125^{\circ}C$	
				Typ	Guaranteed Limits			
$f_{MAX}$	Maximum Operating Frequency	$C_L = 50\text{ pF}$	2.0V	10	5	4	4	MHz
			4.5V	45	27	21	18	MHz
			6.0V	55	32	25	21	MHz
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay from Clock to Q	$C_L = 50\text{ pF}$	2.0V	80	175	220	262	ns
			2.0V	110	225	280	338	ns
		$C_L = 150\text{ pF}$	4.5V	23	35	44	53	ns
			4.5V	28	45	56	68	ns
$t_{PHL}$	Maximum Propagation Delay from Clear to Q	$C_L = 50\text{ pF}$	2.0V	70	150	189	224	ns
			2.0V	100	200	252	298	ns
		$C_L = 150\text{ pF}$	4.5V	20	30	38	45	ns
			4.5V	25	40	50	60	ns
$t_{PZH}, t_{PZL}$	Maximum Output Enable Time	$R_L = 1\text{ k}\Omega$	2.0V	70	150	189	224	ns
			2.0V	100	200	252	298	ns
		$C_L = 50\text{ pF}$	4.5V	20	30	38	45	ns
			4.5V	25	40	50	60	ns
$t_{PHZ}, t_{PLZ}$	Maximum Output Disable Time	$R_L = 1\text{ k}\Omega$	2.0V	70	150	189	224	ns
			2.0V	100	200	252	298	ns
		$C_L = 50\text{ pF}$	4.5V	20	30	38	45	ns
			4.5V	25	40	50	60	ns
$t_S$	Minimum Data or Data Enable Setup Time		2.0V		100	125	150	ns
			4.5V		20	25	30	ns
			6.0V		17	21	25	ns
$t_{REM}$	Minimum Removal Time		2.0V		90	112	135	ns
			4.5V		18	22	26	ns
			6.0V		15	19	22	ns
$t_H$	Minimum Data or Data Enable Hold Time		2.0V		0	0	0	ns
			4.5V		0	0	0	ns
			6.0V		0	0	0	ns
$t_W$	Minimum Clear or Clock Pulse Width		2.0V	30	80	100	120	ns
			4.5V	9	16	20	24	ns
			6.0V	8	14	17	20	ns

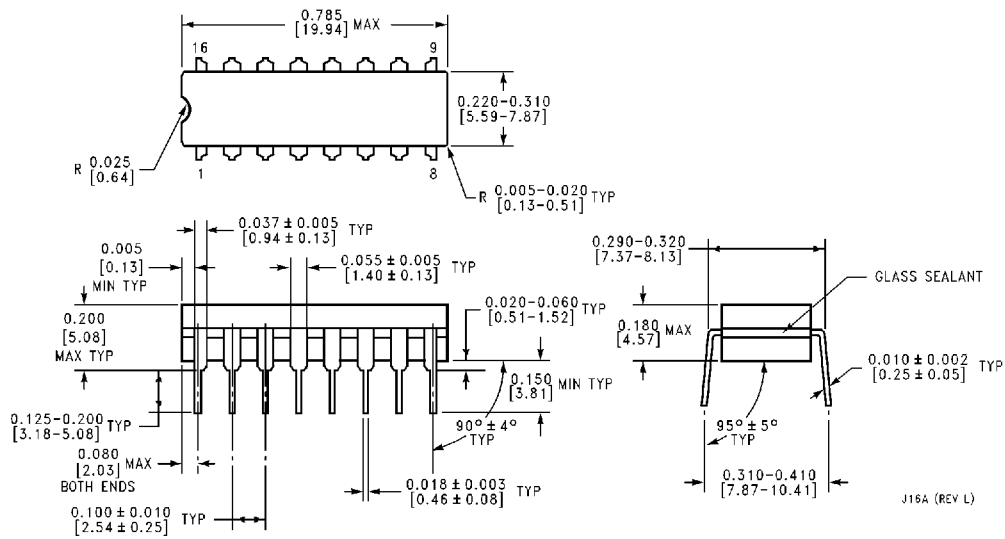
## AC Electrical Characteristics (Continued)

$V_{CC} = 2.0V$  to  $6.0V$ ,  $C_L = 50$  pF,  $t_r = t_f = 6$  ns (unless otherwise specified)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		74HC	54HC	Units
						$T_A = -40$ to $85^\circ C$	$T_A = -55$ to $125^\circ C$	
				Typ	Guaranteed Limits			
$t_{THL}$ , $t_{TLH}$	Maximum Output Rise and Fall Time		2.0V	25	60	75	90	ns
			4.5V	7	12	15	18	ns
			6.0V	5	10	13	15	ns
$t_r$ , $t_f$	Maximum Input Rise and Fall Time		2.0V		1000	1000	1000	ns
			4.5V		500	500	500	ns
			6.0V		400	400	400	ns
$C_{PD}$	Power Dissipation Capacitance	(per flop)		80				pF
$C_{IN}$	Maximum Input Capacitance			5	10	10	10	pF
$C_{OUT}$	Maximum Output Capacitance			10	20	20	20	pF

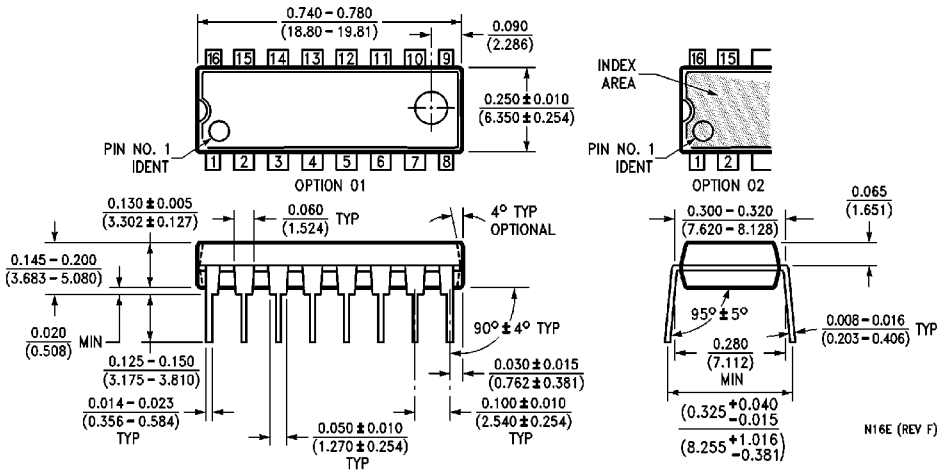
**Note 5:**  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .

**Physical Dimensions** inches (millimeters)



**Dual-In-Line Package**  
**Order Number MM54HC173J or MM74HC173J**  
**NS Package J16A**

**Physical Dimensions** inches (millimeters) (Continued)



**Dual-In-Line Package  
 Order Number MM74HC173N  
 NS Package N16E**

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